# Product / Process Change Notification



N° 2019-032-A

Dear Customer.

Please find attached our INFINEON Technologies PCN:

Introduction of additional wafer production with 8" wafer diameter for IGBT3 3300V (E3) technology and Diode EC3 3300V technology

Important information for your attention:

- Please respond to this PCN by indicating your decision on the approval form, sign it and return to your sales partner before 30<sup>th</sup> April 2019.
- Infineon aligns with the widely-recognized JEDEC STANDARD "JESD46", which stipulates: "Lack of acknowledgement of the PCN within 30 days constitutes acceptance of the change."

Your prompt reply will help Infineon Technologies to assure a smooth and well executed transition. If Infineon does not hear from your side by the due date, we will assume your full acceptance to this proposed change and its implementation.

Your attention and response to this matter is greatly appreciated.

Infineon Technologies AG

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Chairman of the Supervisory Board: Dr. Eckart Sünner

Management Board: Dr. Reinhard Ploss (CEO), Dominik Asam, Dr. Helmut Gassel, Jochen Hanebeck

Registered Office: Neubiberg Commercial Register

Amtsgericht München HRB 126492

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▶ Products affected: IGBT modules with IGBT3 3300V (E3) technology and Diode EC3 3300V

technology in IHV-B housings

Please refer to attached affected product list

"pcn 2019-032-A\_[customer-no].pdf"

# Detailed Change Information:

Subject: Introduction of additional wafer production with

- 8" inch (200mm) wafer diameter for IGBT Chips and

- 8" inch (200mm) wafer diameter for Diode Chips

**Reason:** Capacity extension and increasing security of supply 3300V IGBT and Diode

<u>For IGBTs and Diodes</u> the 8" wafer manufacturing technology is State of the Art' wafer manufacturing technology at Infineon. Therefore, these products will be shifted from 6" inch wafer diameter to 8" inch wafer diameter.

# Description: Old

# ■ IGBT

#### 6 inch

- chip structure with conventional edge termination
- Front end Villach/ Austria

#### <u>New</u>

#### IGBT

#### 6 inch

- chip structure with conventional edge termination:
- Front end Villach/ Austria

#### 8 inch

- chip structure with optimized edge termination:
- Front end Villach/ Austria
- → Target production front end Villach/ Austria 8 inch

## Diode

#### 6 inch

- chip structure with conventional edge termination:
- Front end Villach/ Austria

#### Diode

### 6 inch

- chip structure with conventional edge termination:
- Front end Villach/ Austria

#### 8 inch

- chip structure with optimized edge termination:
- Front end Villach/ Austria
- → Target production front end Villach/ Austria 8 inch

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▶ **Product Identification:** The new modules can be identified by material number, which is part of barcode (digits 6-11) on the module label.

Beside the above mentioned changes, the other specifications of the mentioned modules, like electrical- and mechanical parameters, remain unchanged according to JEDEC Standard JESD46-C: form, fit, function and reliability.

Paralleling of the modules with 6 inch and 8 inch wafer technologies is not recommended.

► Attachments: - Affected product list "pcn\_2019-032-A\_[customer-no].pdf"

- Technical Information is available on request.

▶ Time Schedule:

Final qualification report: On request

First samples available: On request

Intended start of delivery: 2019-June-15 depending on customer approval

If you have any questions, please do not hesitate to contact your local Sales office.

Sales Name	SP Number	OPN
FZ1500R33HE3	SP001181576	FZ1500R33HE3BPSA1
FZ1200R33HE3	SP001181602	FZ1200R33HE3BPSA1
FZ1500R33HE3_B60	SP001617634	FZ1500R33HE3B60BPSA1
FZ1500R33HE3_C1	SP001670374	FZ1500R33HE3C1NPSA1